

Numerical methods for Brillouin zone integration

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Goal:

- Define and compute numerically the **energy per cell** of a crystal.

Crystal? modelled by a periodic, non-interacting Hamiltonian.

Lattice: $\mathcal{R} = a\mathbb{Z}^d$.

Unit cell: $\Gamma = [-a/2, a/2]^d$.

Reciprocal lattice: $\mathcal{R}^* = (2\pi/a)\mathbb{Z}^d$.

Reciprocal unit cell: $\Gamma^* = [-\pi/a, \pi/a]^d$. (**Brillouin zone**)

(mean field) potential: $V_{\text{per}} \in L^2_{\text{per}}(\Gamma)$.

Non-interacting Hamiltonian:

$$H_{\text{per}} = -\frac{1}{2}\Delta + V_{\text{per}}, \quad \text{acting on } L^2(\mathbb{R}^d).$$

Number of electrons per cell: $N \in \mathbb{N}^*$.

Energy (per cell) of the electrons?

Bloch's transform

Studying $H_{\text{per}} \iff$ studying the family of operators $(H_{\mathbf{k}})_{\mathbf{k} \in \Gamma^*}$, where

$$H_{\mathbf{k}} := \frac{1}{2}(-i\nabla_{\text{per}} + \mathbf{k})^2 + V_{\text{per}}, \quad \text{acting on } L^2_{\text{per}}(\Gamma).$$

Remark: The operators $H_{\mathbf{k}}$ are **compact resolvent**:

$$H_{\mathbf{k}} = \sum_{n=1}^{\infty} \varepsilon_{n\mathbf{k}} |u_{n\mathbf{k}}\rangle \langle u_{n\mathbf{k}}|, \quad \varepsilon_{1\mathbf{k}} \leq \varepsilon_{2\mathbf{k}} \leq \dots, \quad \langle u_{n\mathbf{k}}, u_{m\mathbf{k}} \rangle_{L^2_{\text{per}}(\Gamma)} = \delta_{nm}.$$

Integrated density of states (IDoS) (we denote by $f_{\Gamma^*} := \frac{1}{|\Gamma^*|} \int_{\Gamma^*}$)

$$\mathcal{N}(\varepsilon) := \int_{\Gamma^*} \left(\sum_{n>0} \mathbb{1}(\varepsilon_{n\mathbf{k}} \leq \varepsilon) \right) d\mathbf{k}.$$

Fermi energy:

$$\varepsilon_F \in \mathbb{R} \quad \text{such that} \quad \mathcal{N}(\varepsilon_F) = N.$$

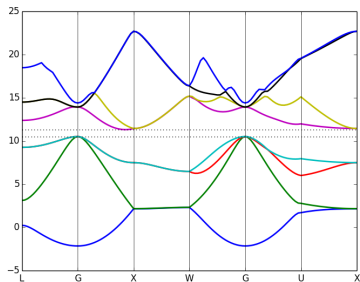
Energy per unit cell

$$E := \int_{\Gamma^*} \left(\sum_{n>0} \varepsilon_{n\mathbf{k}} \mathbb{1}(\varepsilon_{n\mathbf{k}} \leq \varepsilon_F) \right) d\mathbf{k}.$$

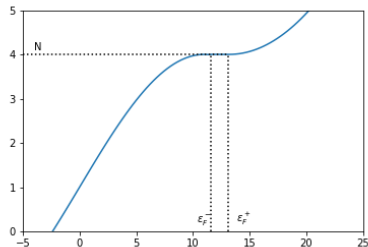
How to perform numerically the Brillouin zone integration \int_{Γ^*} ?

Here, we assume that we can perfectly compute the eigenvalues $\varepsilon_{n\mathbf{k}}$.

Band diagram of silicon (insulator)

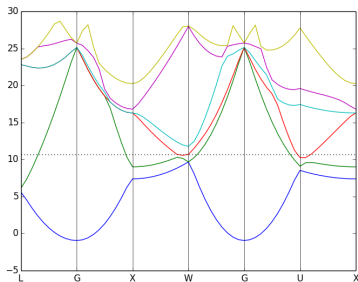


IDoS $\mathcal{N}(\varepsilon)$

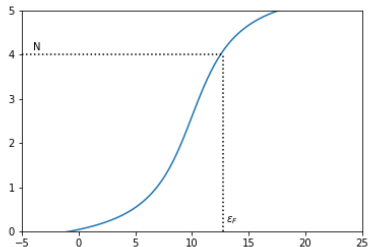


$\mathcal{N}^{-1}(\{N\}) = [\varepsilon_F^-, \varepsilon_F^+]$ is an interval.

Band diagram of aluminium (metal)



IDoS $\mathcal{N}(\varepsilon)$



$\mathcal{N}^{-1}(\{N\}) = \{\varepsilon_F\}$ is unique.

The insulating case

In the insulating case, $\mathbb{1}(\varepsilon_{n\mathbf{k}} < \varepsilon_F) = 1$ if $n \leq N$, and 0 else, hence the energy simplifies into

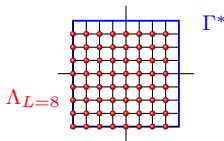
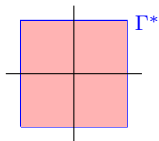
$$E = \int_{\Gamma^*} \left(\sum_{n=1}^N \varepsilon_{n\mathbf{k}} \right) d\mathbf{k}.$$

Lemma

The integrand $\mathbf{k} \mapsto \sum_{n=1}^N \varepsilon_{n\mathbf{k}}$ is analytic and \mathcal{R}^* -periodic. In particular, there exists $C \in \mathbb{R}^+$ and $\alpha > 0$ such that, for all $L \in \mathbb{N}$,

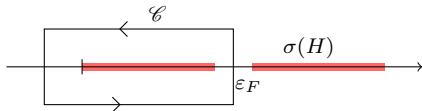
$$\left| \int_{\Gamma^*} \left(\sum_{n=1}^N \varepsilon_{n\mathbf{k}} \right) d\mathbf{k} - \sum_{\mathbf{K} \in \Lambda_L} \left(\sum_{n=1}^N \varepsilon_{n\mathbf{K}} \right) \right| \leq C e^{-\alpha L} \quad (\text{Exponential rate of convergence}).$$

We can approximate the integral with a [Riemann sum](#).



Proof $\mathbf{k} \mapsto H(\mathbf{k})$ is analytic (quadratic), and

$$\sum_{n=1}^N \varepsilon_{n\mathbf{k}} = \text{Tr} \left(\oint_{\mathcal{C}} \frac{H_{\mathbf{k}}}{z - H_{\mathbf{k}}} dz \right).$$



Metallic systems

Problems

- First, we need to compute the Fermi level (extra source of error);
- The integrand is no longer smooth.

Two widely used methods

- Interpolation methods;
- Smearing methods.

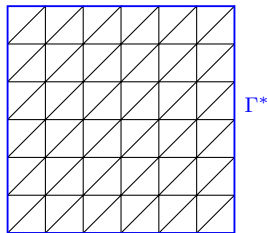
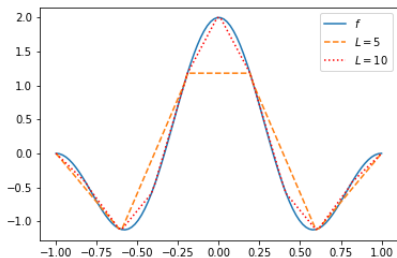
The metallic case. 1/ Interpolation methods

Idea: Approximate $\mathbf{k} \mapsto \varepsilon_{n\mathbf{k}}$ with a simpler function.

A family of **linear interpolation operators** $(\Pi^{L,q})_{L \in \mathbb{N}}$ is of order $(q + 1)$ if

$$\forall f \text{ smooth}, \quad \|f - \Pi^{L,q} f\|_{\infty} \leq \frac{C}{L^{q+1}} \|f^{(q+1)}\|_{\infty}.$$

Example: the *linear tetrahedron method* ($q = 1$).



division of Γ^* in simplexes (for $d = 2$).

Approximated eigenvalues

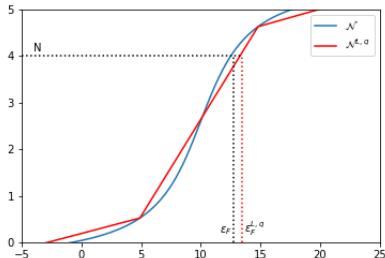
$$\varepsilon_{n\mathbf{k}}^{L,q} := \Pi^{L,q}(\varepsilon_{n\mathbf{k}}).$$

Approximated integrated density of states

$$\mathcal{N}^{L,q}(\varepsilon) := \int_{\Gamma^*} \left(\sum_{n>0} \mathbb{1}(\varepsilon_{n\mathbf{k}}^{L,q} \leq \varepsilon) \right) d\mathbf{k}.$$

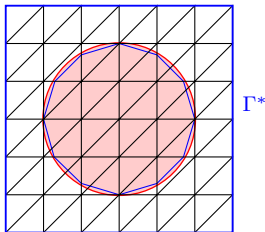
Approximated Fermi energy

$$\varepsilon_F^{L,q} \in \mathbb{R} \quad \text{such that} \quad \mathcal{N}^{L,q}(\varepsilon_F^{L,q}) = N.$$



Approximated energy per unit cell

$$E^{L,p,q} := \int_{\Gamma^*} \left(\sum_{n>0} \varepsilon_{n\mathbf{k}}^{L,p} \mathbb{1}(\varepsilon_{n\mathbf{k}}^{L,q} \leq \varepsilon_F) \right) d\mathbf{k}.$$



- $q \implies$ the domain of integration (here still a union of simplexes).
- $p \implies$ degree of the polynomial to integrate on this domain.

In practice, $p \geq q$. (we can integrate quadratic functions ($p=2$) on simplexes ($q=1$)).

Assumptions:

- No band-crossings at the Fermi level;
- No flat bands at the Fermi level ($\nabla_{\mathbf{k}} \varepsilon_{n\mathbf{k}} \neq \mathbf{0}$).

⇒ The function $\mathcal{N}(\varepsilon)$ is smooth near the Fermi level.

Lemma (Cancès, Ehrlicher, G., Levitt, Lombardi)

Let $(\Pi^{L,q})_{L \in \mathbb{N}}$ and $(\Pi^{L,p})_{L \in \mathbb{N}}$ be linear interpolation operators of order $(q+1)$ and $(p+1)$ respectively. Then, under the previous assumptions, there exists $\delta > 0$ and $C \in \mathbb{R}^+$ such that, for all $L \in \mathbb{N}$,

$$\max_{\varepsilon \in (\varepsilon_F - \delta, \varepsilon_F + \delta)} \left| \mathcal{N}(\varepsilon) - \mathcal{N}^{L,q}(\varepsilon) \right| \leq \frac{C}{L^{q+1}}, \quad \left| \varepsilon_F - \varepsilon_F^{L,q} \right| \leq \frac{C}{L^{q+1}},$$

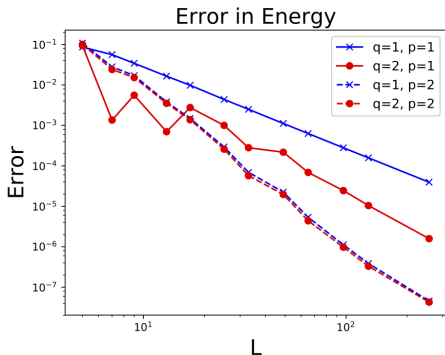
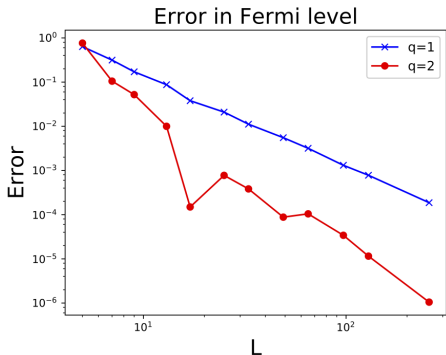
and

$$\left| E - E^{L,p,q} \right| \leq C \left(\frac{1}{L^{p+1}} + \frac{1}{L^{2q+2}} \right).$$

Remarks:

- The $L^{-(p+1)}$ comes from the *bulk error*, while the $L^{-(2q+2)}$ comes from the *surface error*.
- For tetrahedron methods ($q = 1$), we can choose $p = 3$ (low computational cost, but better precision for the energy). This leads to $O(L^{-4})$ rate of convergence.
- The last result only works for the energy.

Results (toy model, not coming from a Schrödinger operator)



The metallic case. 2/ Smearing methods

Idea: Replace the discontinuous function $f(x) := \mathbf{1}(x < 0)$ by a smooth function f^σ .

Smearing functions

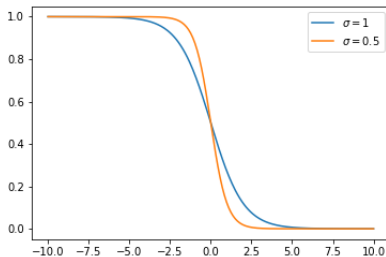
$$f^\sigma(x) := f^1(x/\sigma) \quad \text{where } (f - f^1) \text{ decays exponentially}$$

Definition f^1 is of order $p \in \mathbb{N}$ if

$$\int_{\mathbb{R}} (f - f^1)(x)P(x)dx = 0 \quad \text{for all polynomials } P \text{ of degree } \leq p,$$

Example: Fermi-Dirac (of order 1)

$$f^\sigma(x) := \frac{1}{1 + e^{x/\sigma}}.$$



Smearing integrated density of states

$$\mathcal{N}^\sigma(\varepsilon) := \int_{\Gamma^*} \left(\sum_{n>0} f^\sigma(\varepsilon_{n\mathbf{k}} - \varepsilon) \right) d\mathbf{k}.$$

Smearing Fermi level

$$\varepsilon_F^\sigma \in \mathbb{R} \quad \text{such that} \quad \mathcal{N}^\sigma(\varepsilon_F^\sigma) = N.$$

Smearing energy per unit cell

$$E^\sigma := \int_{\Gamma^*} \left(\sum_{n>0} \varepsilon_{n\mathbf{k}} f^\sigma(\varepsilon_{n\mathbf{k}} - \varepsilon_F^\sigma) \right) d\mathbf{k}.$$

Lemma (Cancès, Ehrlicher, G., Levitt, Lombardi)

Let f^1 be a smearing function of order $p \in \mathbb{N}$. Under the previous assumptions, there exists $\delta > 0$ and $C \in \mathbb{N}^+$ such that, for all $\sigma > 0$,

$$\max_{\varepsilon \in (\varepsilon_F - \delta, \varepsilon_F + \delta)} |\mathcal{N}(\varepsilon) - \mathcal{N}^\sigma(\varepsilon)| \leq C\sigma^{p+1}, \quad |\varepsilon_F - \varepsilon_F^\sigma| \leq C\sigma^{p+1}, \quad \text{and} \quad |E - E^\sigma| \leq C\sigma^{p+1},$$

Idea of the proof

- near the Fermi level, \mathcal{N} is smooth \implies perform Taylor expansion;
- far from the Fermi level, $(f - f^\sigma)(\cdot - \varepsilon_F)$ decays exponentially.

Remark: We still need to find a numerical method to approximate \mathcal{N}^σ , ε_F^σ and E^σ . Recall that,

$$\mathcal{N}^\sigma(\varepsilon) := \int_{\Gamma^*} \left(\sum_{n>0} f^\sigma(\varepsilon_{n\mathbf{k}} - \varepsilon) \right) d\mathbf{k}.$$

Lemma (for the Fermi-Dirac function)

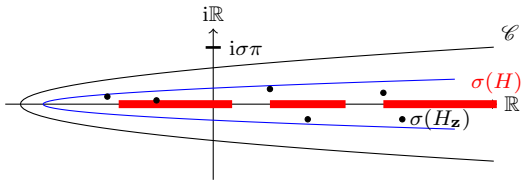
For all ε in a neighbourhood of ε_F , and all $\sigma > 0$, the integrand $\mathbf{k} \mapsto \sum_{n>0} f^\sigma(\varepsilon_{n\mathbf{k}} - \varepsilon)$ is \mathcal{R}^* -periodic and analytic in a complex strip of width ($\text{cst} \cdot \sigma$). In particular, there exists $C \in \mathbb{R}^+$ and $\alpha > 0$, such that

$$\left| \int_{\Gamma^*} \left(\sum_{n>0} f^\sigma(\varepsilon_{n\mathbf{k}} - \varepsilon) \right) d\mathbf{k} - \sum_{\mathbf{K} \in \Lambda_L} \left(\sum_{n>0} f^\sigma(\varepsilon_{n\mathbf{K}} - \varepsilon) \right) \right| \leq C\sigma^{-(d+1)}e^{-\alpha\sigma L}.$$

Again, we can approximate the integral with a [Riemann sum](#).

Idea of the proof

$$\sum_{n>0} f^\sigma(\varepsilon_{n\mathbf{k}} - \varepsilon) = \text{Tr} \left(\oint_{\mathcal{C}} \frac{f^\sigma(z)}{z - H_{\mathbf{k}}} dz \right).$$



Conclusion

Insulators with Riemann sum

$$\left| E - E^L \right| \leq C e^{-\alpha L}.$$

Metals with interpolation methods of order p and q ,

$$\left| E - E^{L,p,q} \right| \leq C \left(\frac{1}{L^{p+1}} + \frac{1}{L^{2q+2}} \right).$$

Metals with smearing methods of order p

$$\left| E - E^{\sigma,L} \right| \leq |E - E^\sigma| + \left| E^\sigma - E^{\sigma,L} \right| \leq C \left(\sigma^{p+1} + \sigma^{-(d+1)} e^{-\alpha \sigma L} \right).$$

Choosing $\sigma \approx \sigma_L := L^{-1^+}$,

$$\left| E - E^{\sigma_L,L} \right| \leq \frac{C}{L^{(p+1)^-}}.$$

- É. Cancès, V. Ehrlicher, D. Gontier, A. Levitt, D. Lombardi. *Numerical quadrature in the Brillouin zone for periodic Schrödinger operators*. (in preparation, but should be on arXiv very soon).